



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#8/Donald A
A. trial
1/27/01

Patent Application of)

Akihiko ISHIBASHI et al.)

Art Unit: 2812

Serial No. 09/692,211)

Filed: October 20, 2000)

Examiner: S. MULPURI

For: METHOD OF FABRICATING)

NITRIDE SEMICONDUCTOR DEVICE)

AMENDMENT UNDER 37 C.F.R. 1.111

Honorable Commissioner of Patents
Washington, D.C. 20231

November 27, 2001

Sir:

In response to the Office Action dated August 1, 2001, please amend the above-identified application and consider Applicants' remarks as follows:

IN THE CLAIMS:

Please amend claims 1 and 8 as follows.

1. (Amended) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising:

plural steps of respectively growing plural nitride semiconductor layers on a substrate;

and

between a step of growing one nitride semiconductor layer and a step of growing another nitride semiconductor layer adjacent to said one nitride semiconductor layer among the plural steps, a step of changing a growth ambient pressure from a first growth ambient pressure to a second growth ambient pressure different from said first growth ambient pressure.

8. (Amended) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising the steps of:

forming plural seed crystals on a substrate;